

L Number	Hits	Search Text	DB	Time stamp
1	44271	sic or (silicon adj carbide)	USPAT;	2002/11/12 08:13
			US-PGPUB	
2	6785	(sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 08:13
		mosfet)	US-PGPUB	
3	373	((sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 08:32
		mosfet)) and (anneal\$4 same ("h.sub.2" or hydrogen))	US-PGPUB	
4	225	((sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 07:59
		mosfet)) and (anneal\$4 near12 ("h.sub.2" or hydrogen))	US-PGPUB	
5	41	(sic or (silicon adj carbide)) same (anneal\$4 near12	USPAT;	2002/11/12 08:13
		("h.sub.2" or hydrogen))	US-PGPUB	
6	25	((sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 07:55
		mosfet)) and ((sic or (silicon adj carbide)) same (anneal\$4	US-PGPUB	
		near12 ("h.sub.2" or hydrogen)))		
7	1163	(nitrid\$8 or "n.sub.2 o" or "no" or (nitrous adj oxide) or (nitric	USPAT;	2002/11/12 08:11
		adj oxide) or nitrogenation) same (anneal\$4 near12	US-PGPUB	
'		("h.sub.2" or hydrogen))	LIODAT.	0000/44/40 00:04
8	66	((sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 08:01
		mosfet)) and ((nitrid\$8 or "n.sub.2 o" or "no" or (nitrous adj	US-PGPUB	
		oxide) or (nitric adj oxide) or nitrogenation) same (anneal\$4		
10	0	near12 ("h.sub.2" or hydrogen))) ((oxynitrid\$8) same (anneal\$4 near12 ("h.sub.2" or	USPAT;	2002/11/12 08:11
10	U	hydrogen))) and ((sic or (silicon adj carbide)) same	US-PGPUB	2002/11/12 00.11
		(semiconductor or mos or mosfet))	00-1-01-05	
11	1	((oxynitrid\$8) same (anneal\$4 near12 ("h.sub.2" or	USPAT;	2002/11/12 08:11
' '	'	hydrogen))) and (sic or (silicon adj carbide))	US-PGPUB	2002/11/12 00:17
9	43	(oxynitrid\$8) same (anneal\$4 near12 ("h.sub.2" or hydrogen))	USPAT;	2002/11/12 08:12
	,,,	((((US-PGPUB	
12	56448	sic or (silicon adj carbide)	EPO; JPO;	2002/11/12 08:13
		, ,	DERWENT;	
			IBM_TDB	
13	5373	(sic or (silicon adj carbide)) same (semiconductor or mos or	EPO; JPO;	2002/11/12 08:36
		mosfet)	DERWENT;	
		,	IBM_TDB	
14	12	((sic or (silicon adj carbide)) same (semiconductor or mos or	EPO; JPO;	2002/11/12 08:13
		mosfet)) and (anneal\$4 near12 ("h.sub.2" or hydrogen))	DERWENT;	
			IBM_TDB	
15	20	((sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 08:34
		mosfet)) same (anneal\$4 same ("h.sub.2" or hydrogen))	US-PGPUB	
16	24	((sic or (silicon adj carbide)) same (semiconductor or mos or	USPAT;	2002/11/12 08:35
	_	mosfet)) same ("n.sub.2 o")	US-PGPUB	00004440 00 07
17	2	((sic or (silicon adj carbide)) same (semiconductor or mos or	EPO; JPO;	2002/11/12 08:37
		mosfet)) same ("n.sub.2 o" or n2o)	DERWENT;	
			IBM_TDB	